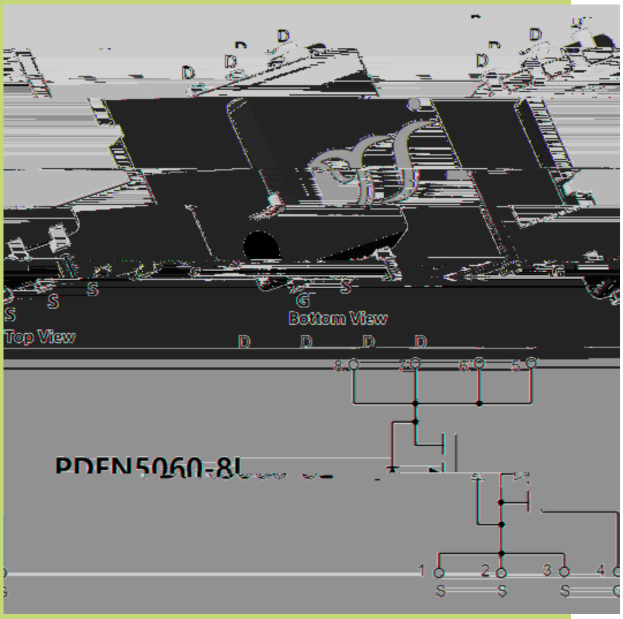
RoHS
COMPLIANT

G300G04HRQ

nent Mode Field Effect Transistor



Product Summary

- ● V_{DS} 40V
- ● I_D 300A
- ● $R_{DS(ON)}$(at V_{GS}=10V) 0.85mΩ
- ● 100% EAS Tested
- ● 100% V_{DS} Tested

General Description

- ● Split gate trench MOSFET technology
- ● Excellent package for heat dissipation
- ● High density cell design for low $R_{DS(OO}$

ls ■ Absolute Maximum Ratings (Ŧ25 Ņ unl

Symbol	Limit	Unit
V_{DS}	40	V
V_{GS}	±20	V
I_D	43	A
	30	
	300	
	212	

I

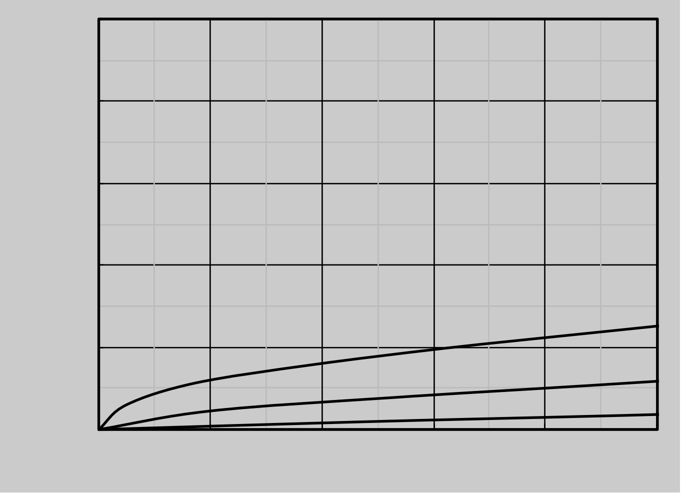
EAS	1458	mJ
P_D	3	W
	1.5	
	136	
	68	
T_J ,T_{STG}	-55 +175	

PREFERED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJG300G04HRQ	F1	G300G04HR	5000	10000	100000	13“ reel

■ **Electrical Characteristics** (T_J=25 unless otherwise noted)

Parameter	Symbol	Conditions	Min	

ÿTypical Electrical and Thermal Characteristics Diagrams



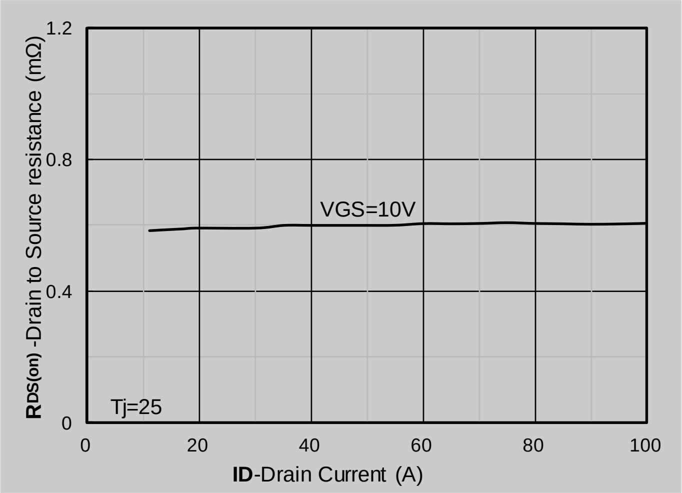


Figure 7. RDS(on) VS Drain Current

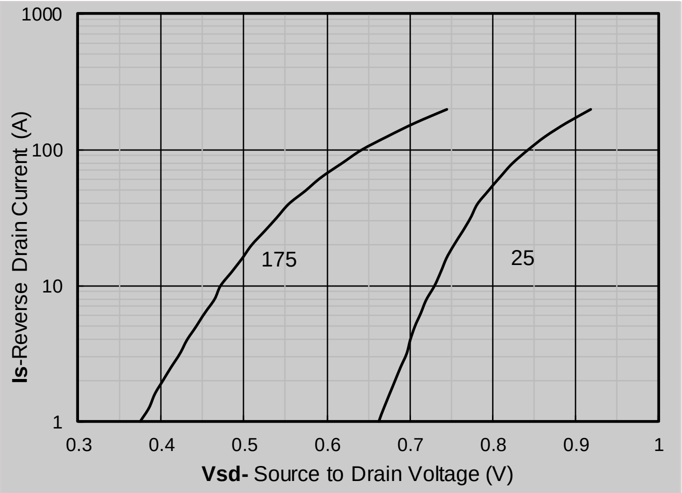


Figure 8. Forward characteristics of reverse diode

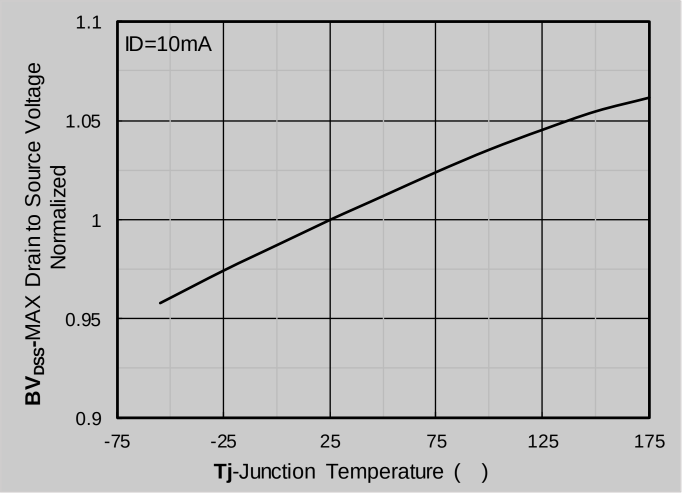


Figure 9. Normalized breakdown voltage

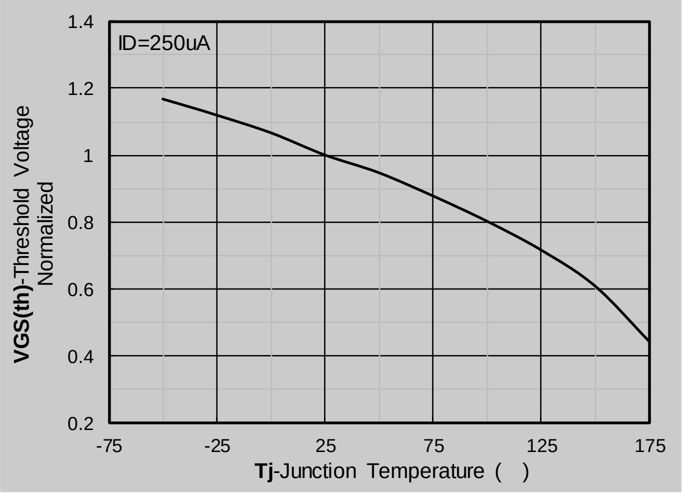
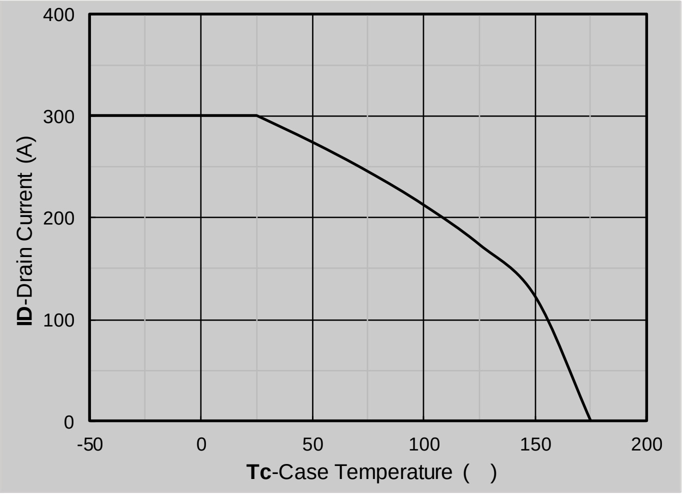


Figure 10. Normalized Threshold voltage



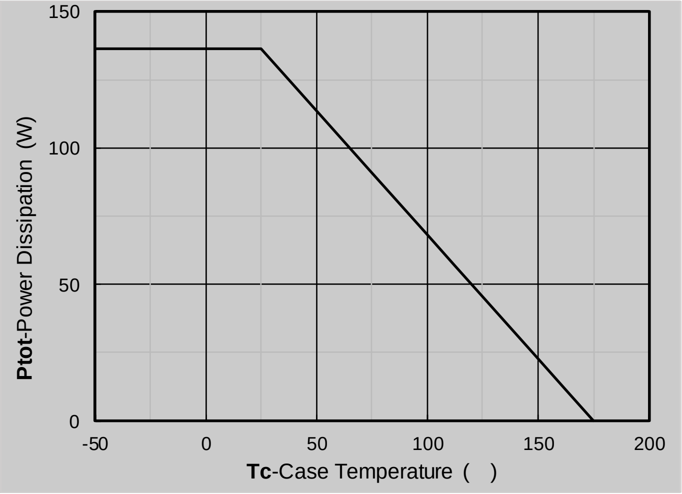


Figure 11. Current dissipati

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'LVFODLPHU

7KH LQIRUPDWLRQ SUHVHQWHG LQ WK\LV<DQJ]KRX<DQJMLH (OHFWURQLF7HFKQRO
ULJKW WR PDNH FKDQJHVUZLWKRXW WKH SURSHU QRWLFH RI GLVSOD\HG KHUHLQ WRGLHPVSLURY
RWKHUZLVH

7KH SURGXFW OLVWLQJHGHWHUPLQHG E\ DXWKRU LQ WKH FDWHJRU\ RI DGYHUWLVHPHQW GHVLJQ PHGLFDO OLIH
VDYLQJ OLIHVXVWDLQLQJ <DQJMLH RU DOO LWV HQG XVHUV DJUHH WR IXOO\ LQGHPQLI\ DQG KROG <DQJMLH
VXFK LPSURSHU XVH RI VDOH

7KLV SXEOLFDWLRQ VXSHUVHGHV DQG UHSODFHV DOO LQIRUPDWLRQ SUHYLRXVO\ VXSSOLHG
ZZZ \DQJMLHFRP FRQVXOW \RXU VDOHV UHSUHVHQWDWLYH